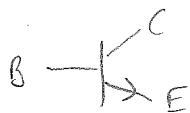


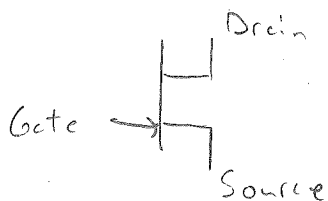
Regular transistor



"bipolar" or "bipolar junction" transistor

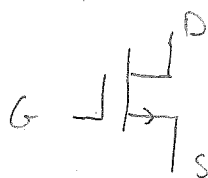
Another type: Field Effect Transistor (FET)

JFET



(no good reason for new names)

MOSFET



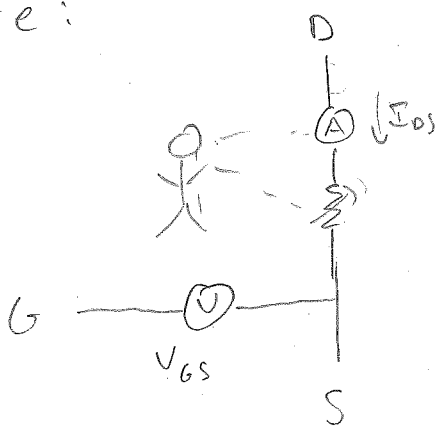
Same basic idea: I_{DS} controlled by gate

But now controlled by gate voltage, not current

I_G nearly zero

⇒ very high input impedance
low power dissipation

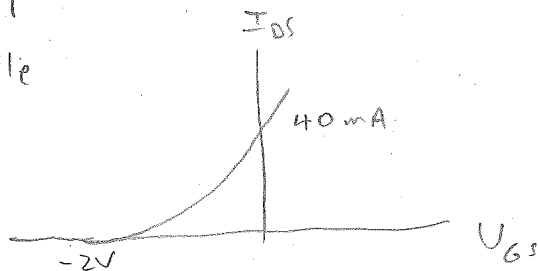
Picture:



"FET man" adjusts R_{DS} according to V_{GS}

Uses a particular function $I(V_{GS})$

Example



But varies by type of FET,

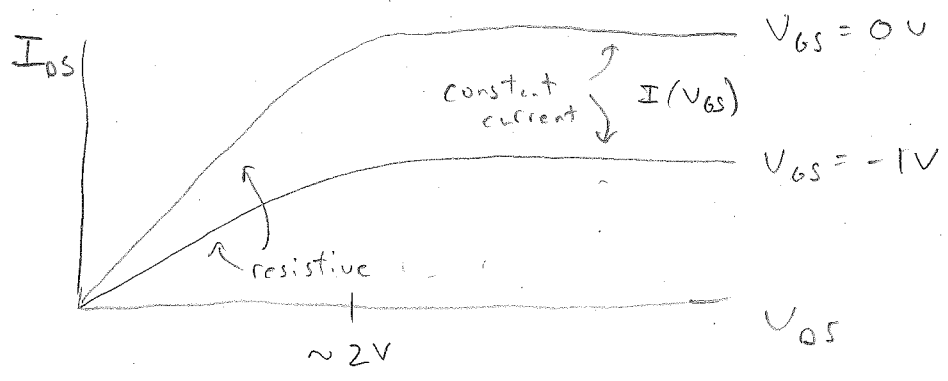
- from device to device,
with temperature

Like bipolar transistor, only works right if V_{DS} is large enough

For small V_{DS} , acts like a resistor R_{DS}

\Rightarrow FET men's potentiometer doesn't go to zero

But R_{min} does depend on V_{GS}

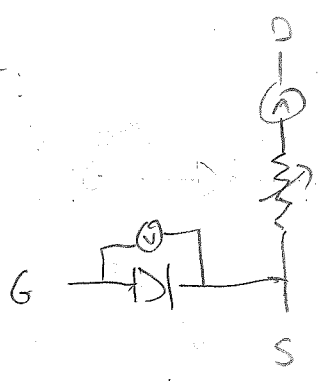


(If you ask for more current, FET men tries harder to turn pot down to zero.)

Two major types: MOSFET + JFET

differ on gate coupling

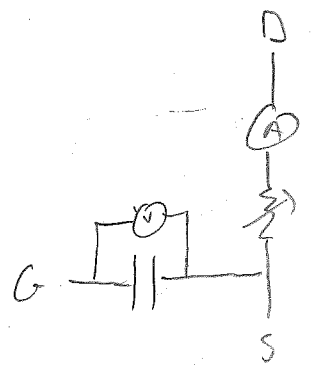
JFET:



Diode from G to S (like npn transistor)

But don't want any gate current
Need to keep $V_{GS} <$ diode drop
typically $V_{GS} < 0$

MOSFET

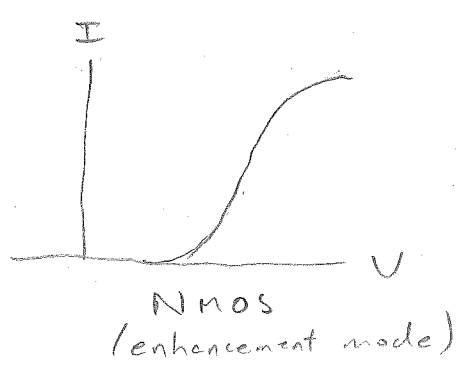
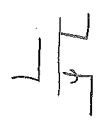
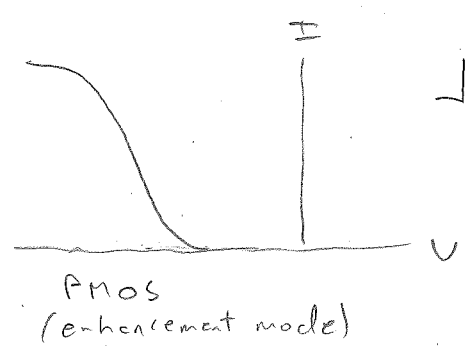
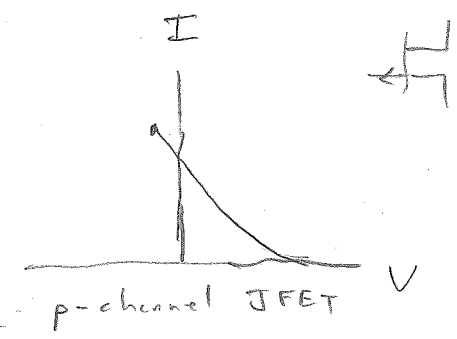
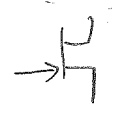
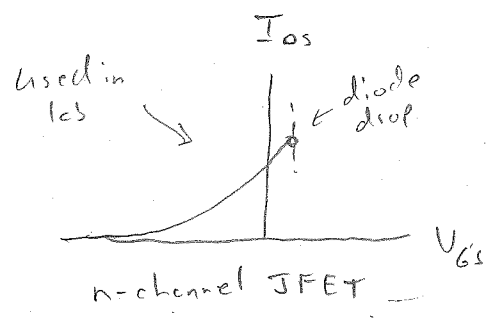


Capacitor from G to S
 \Rightarrow no dc current

But large V_{GS} breaks capacitor!
Need to be careful of static electricity

Besides this, there are a bunch of subtypes
Different functions $I_{DS}(V_{GS})$

Four main types:



(symbols vary)

Impossible to keep track of names if you don't work with FETs a lot.

Just remember each FET has its own $I_D(V_{GS})$ function, get from data sheet.

Comparison to bipolar transistors:

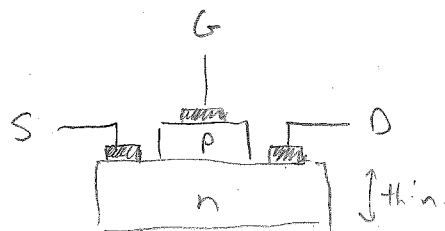
BJT's typically have higher gain & current capacity

FET's don't need control current: simplifies design & reduces power consumption

Done

Physics:

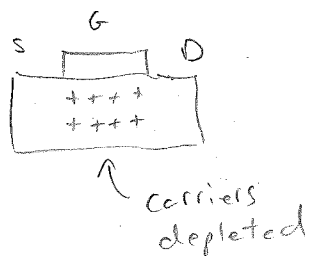
JFET:
(n-channel)



An junction forms diode, as usual

Get conduction from D to S via n-doped material (electron carriers)

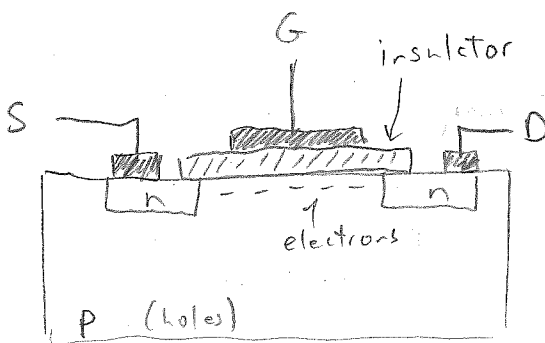
Apply $V_G < 0$: pushes electrons away from gate region



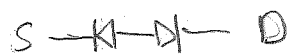
Increases resistance R_{DS}

Big enough V_G , $I_{DS} \rightarrow 0$

MOSFET:
(NMOS enhancement)



Here $D \rightarrow S$ looks like two diodes!



no conduction

If $V_G > 0$ applied, holes repelled from gate region
Large enough V_G , electrons pulled into conduction band

- => material starts to look n-type
- => get conduction